

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

## 2SA1832FT

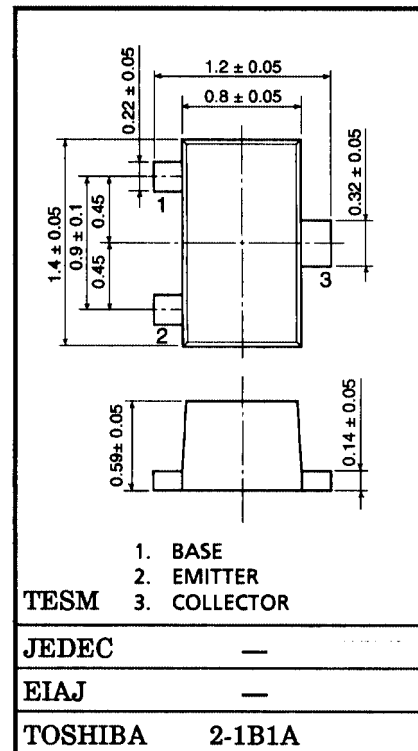
Audio frequency General Purpose Amplifier Applications

- High voltage:  $V_{CEO} = -50\text{ V}$
- High current:  $I_C = -150\text{ mA (max)}$
- High  $h_{FE}$ :  $h_{FE} = 120\text{ to }400$
- Excellent  $h_{FE}$  linearity:  $h_{FE} (I_C = -0.1\text{ mA}) / h_{FE} (I_C = -2\text{ mA}) = 0.95\text{ (typ.)}$
- Complementary to 2SC4738F

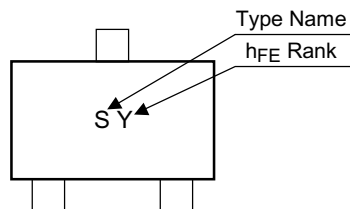
### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-150	mA
Base current	$I_B$	-30	mW
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to 125	$^\circ\text{C}$

Unit in mm



### Marking



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## Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$ (Note)	$V_{CE} = -6\text{ V}, I_B = -2\text{ mA}$	120	—	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{ mA}, I_B = -10\text{ mA}$	—	-0.1	-0.3	V
Transition frequency	$f_T$	$V_{CE} = -10\text{ V}, I_C = -1\text{ mA}$	80	—	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	4	7	pF

Note:  $h_{FE}$  Classification Y (Y): 120 to 140, GR (G): 200 to 400

( ) Marking symbol

